

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC3515

HIGH VOLTAGE CONTROL APPLICATIONS
PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS
CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS

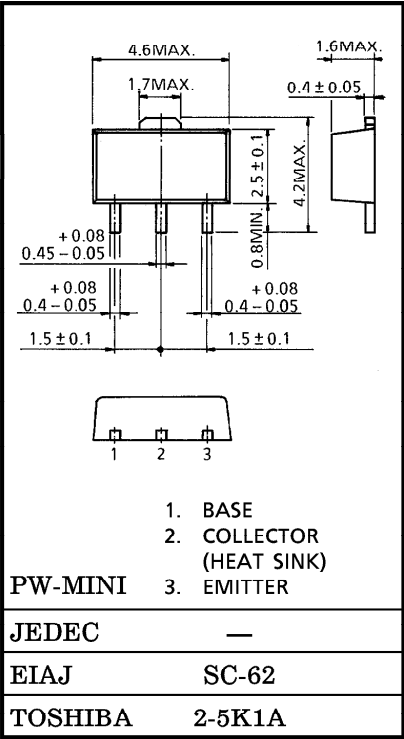
- High Voltage : $V_{CBO}=300V$, $V_{CEO}=300V$
- Low Saturation Voltage : $V_{CE(sat)}=0.5V$ (Max.)
- Small Collector Output Capacitance : $C_{ob}=3pF$ (Typ.)
- Complementary to 2SA1384
- Small Flat Package
- $P_C=1\sim2W$ (Mounted Ceramic Substrate)

MAXIMUM RATINGS (Ta = 25°C)

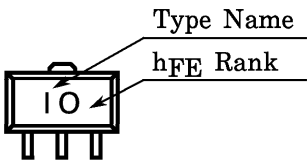
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	1000	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Note : Mounted on ceramic substrate (250mm²×0.8mmt)

Unit in mm



Marking



961001EAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 300V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR) CBO}$	$I_C = 0.1mA, I_E = 0$	300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 1mA, I_B = 0$	300	—	—	V
DC Current Gain	$h_{FE (1)}$ (Note)	$V_{CE} = 10V, I_C = 20mA$	30	—	150	
	$h_{FE (2)}$	$V_{CE} = 10V, I_C = 1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE (sat)}$	$I_C = 20mA, I_B = 2mA$	—	—	0.5	V
Base-Emitter Saturation Voltage	$V_{BE (sat)}$	$I_C = 20mA, I_B = 2mA$	—	—	1.0	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 20mA$	50	80	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 20V, I_E = 0, f = 1MHz$	—	3	4	pF

Note : $h_{FE (1)}$ Classification R : 30~90, O : 50~150

